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FL6L52010L

Silicon P-channel MOSFET(FET)
 Silicon epitaxial planar type(SBD)

For switching
 For DC-DC Converter

■ Features

- Low drain-source ON resistance : $R_{DS(on)}$ typ. = 80 mΩ (VGS = -4.0 V)
- Low drive voltage : 1.8 V drive
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : Y1

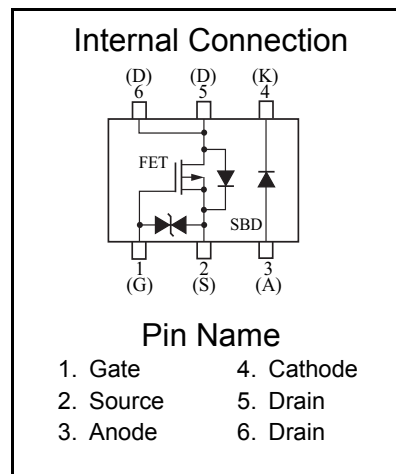
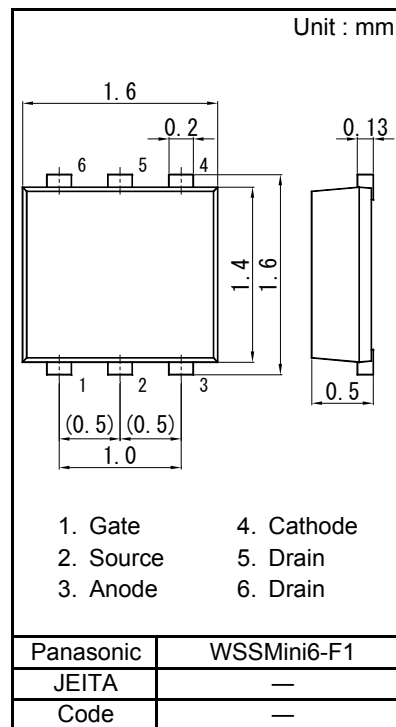
■ Packaging

Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

項目		Symbol	Rating	Unit
FET	Drain to Source Voltage	VDS	-20	V
	Gate to Source Voltage	VGS	±10	V
	Drain current	ID	-2.0	A
	Peak drain current	IDp	-8.0	A
	Channel temperature	Tch	150	°C
SBD	Reverse voltage	VR	20	V
	Forward current (Average)	IF(AV)	800	mA
	Junction temperature	Tj	125	°C
Overall	Operating ambient temperature	Topr	-40 to +85	°C
	Storage temperature	Tstg	-55 to +125	°C
	Total power dissipation*1	PD	540	mW

Note: *1 Measuring on ceramic substrate at 40 mm × 38 mm × 0.2 mm
 PD absolute maximum rating without a heat sink: 150 mW



■ Electrical Characteristics Ta = 25 °C ± 3 °C
 FET (P-ch.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	VDSS	ID = -1.0 mA, VGS = 0	-20			V
Drain-source cutoff current	IDSS	VDS = -20 V, VGS = 0			-1.0	μA
Gate-source cutoff current	IGSS	VGS = ±8 V, VDS = 0			±10	μA
Gate threshold voltage	VTH	ID = -1.0 mA, VDS = -10 V	-0.4	-0.75	-1.1	V
Drain-source ON resistance *1	RDS(on)1	ID = -1.0 A, VGS = -4.0 V		80	120	mΩ
	RDS(on)2	ID = -1.0 A, VGS = -2.5 V		100	170	
	RDS(on)3	ID = -0.5 A, VGS = -1.8 V		140	230	
Forward transfer admittance *1	Yfs	ID = -1.0 A, VDS = -10 V, f = 1 kHz	3.0			S
Short-circuit input capacitance (Common source)	Ciss	VDS = -10 V, VGS = 0, f = 1 MHz		300		pF
Short-circuit output capacitance (Common source)	Coss			30		
Reverse transfer capacitance (Common source)	Crss			35		
Turn-on delay time *2	td(on)	VDD = -10 V, VGS = 0 V to -4 V		6		ns
Rise time *2	tr	ID = -1.0 A		8		
Turn-off delay time *2	td(off)	VDD = -10 V, VGS = -4 V to 0 V		57		ns
Fall time *2	tf	ID = -1.0 A		55		

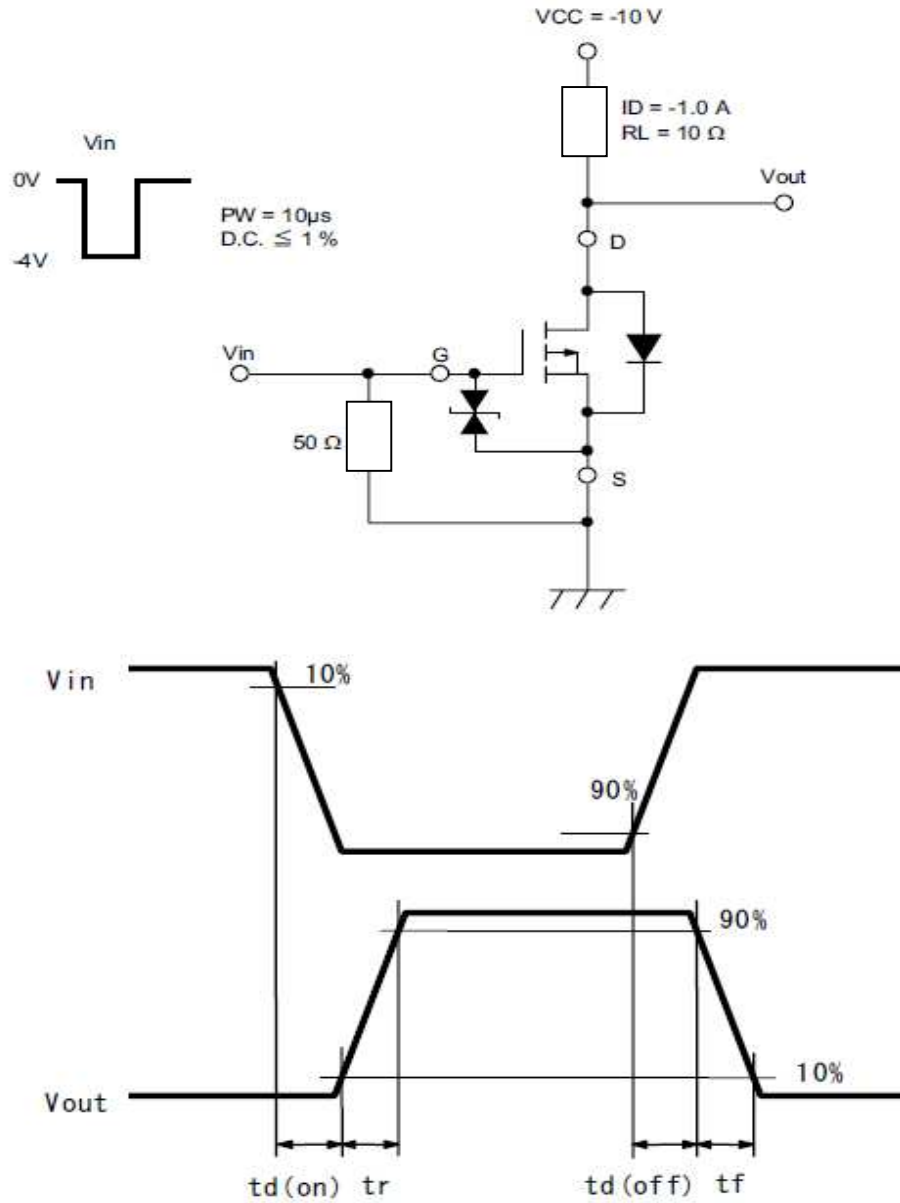
Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.
 2. *1 Pulse measurement
 *2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

SBD

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 800 mA			0.47	V
Reverse current	IR	VR = 20 V			80	μA

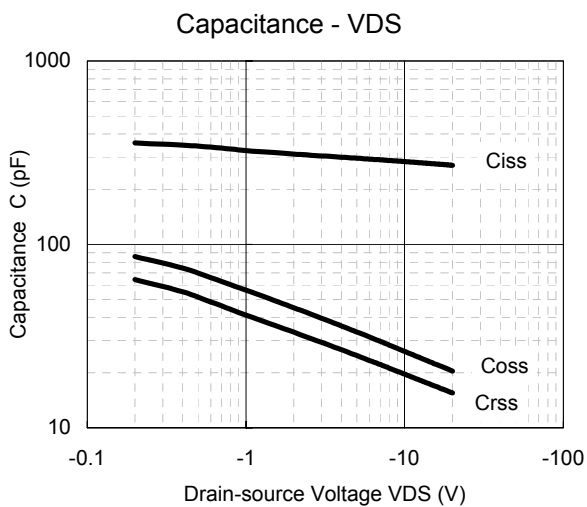
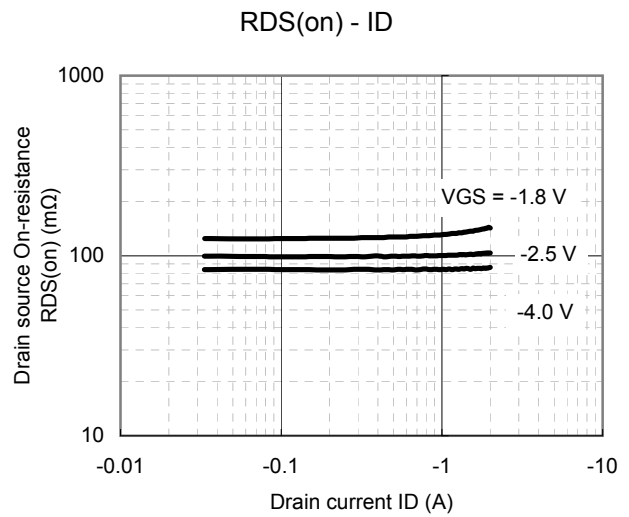
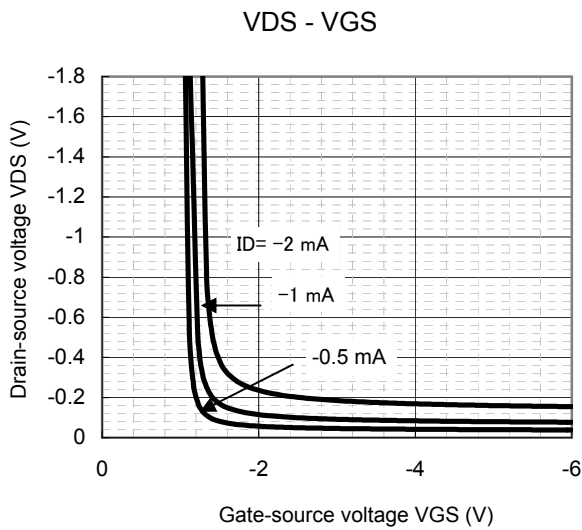
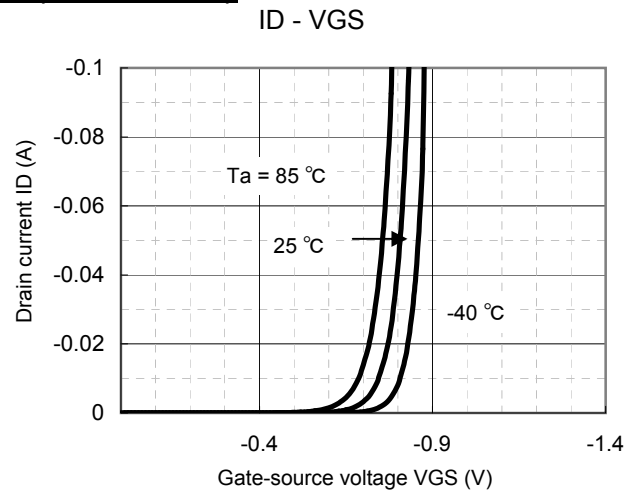
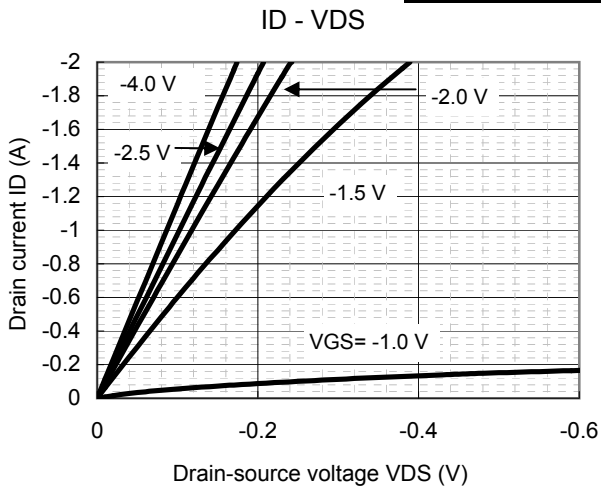
Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



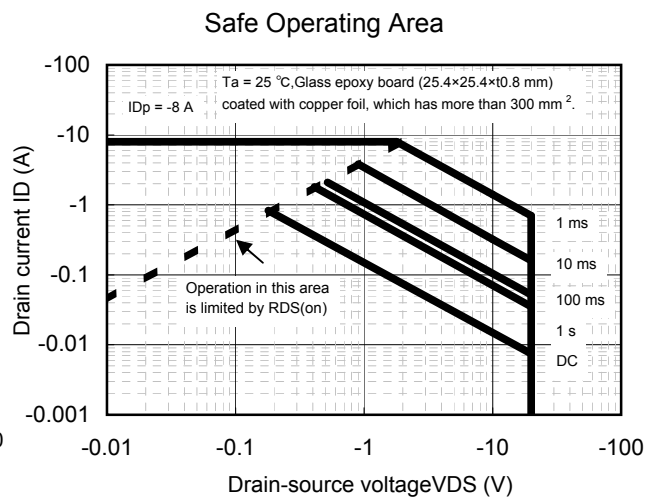
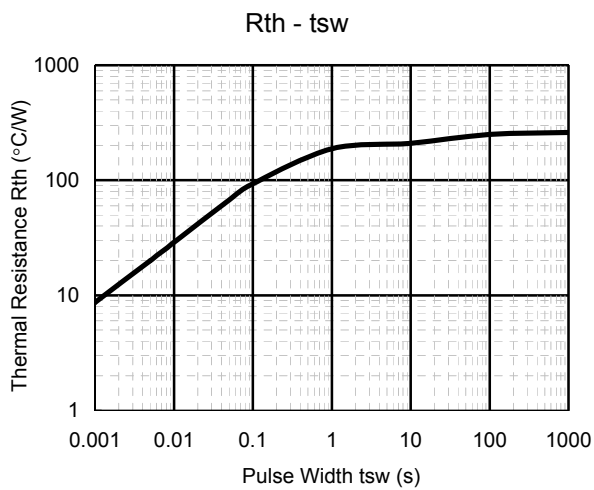
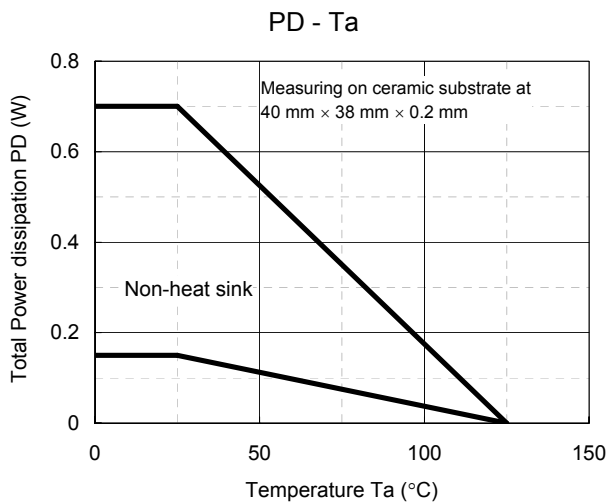
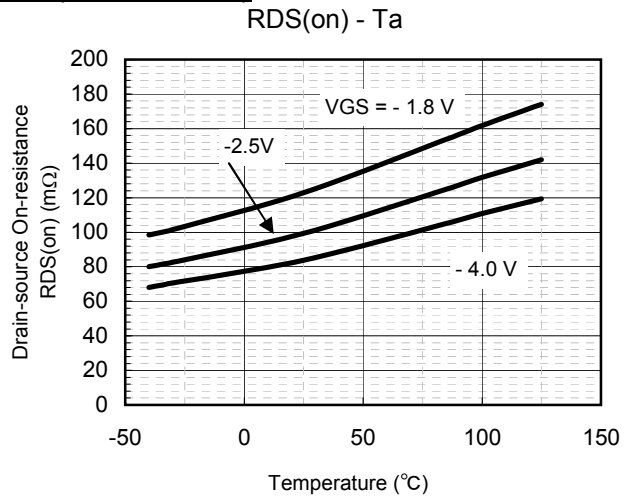
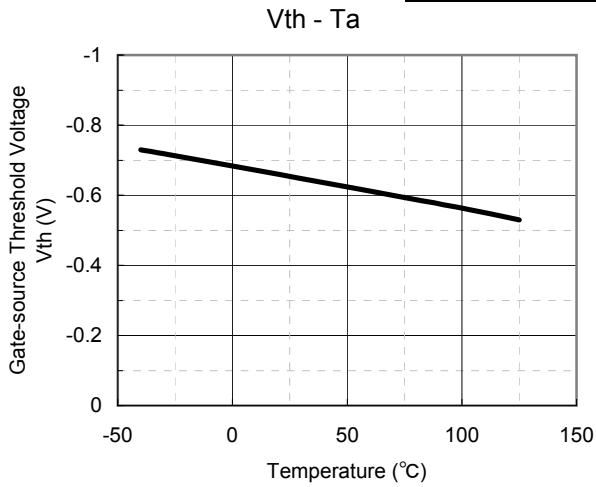


Technical Data (reference)



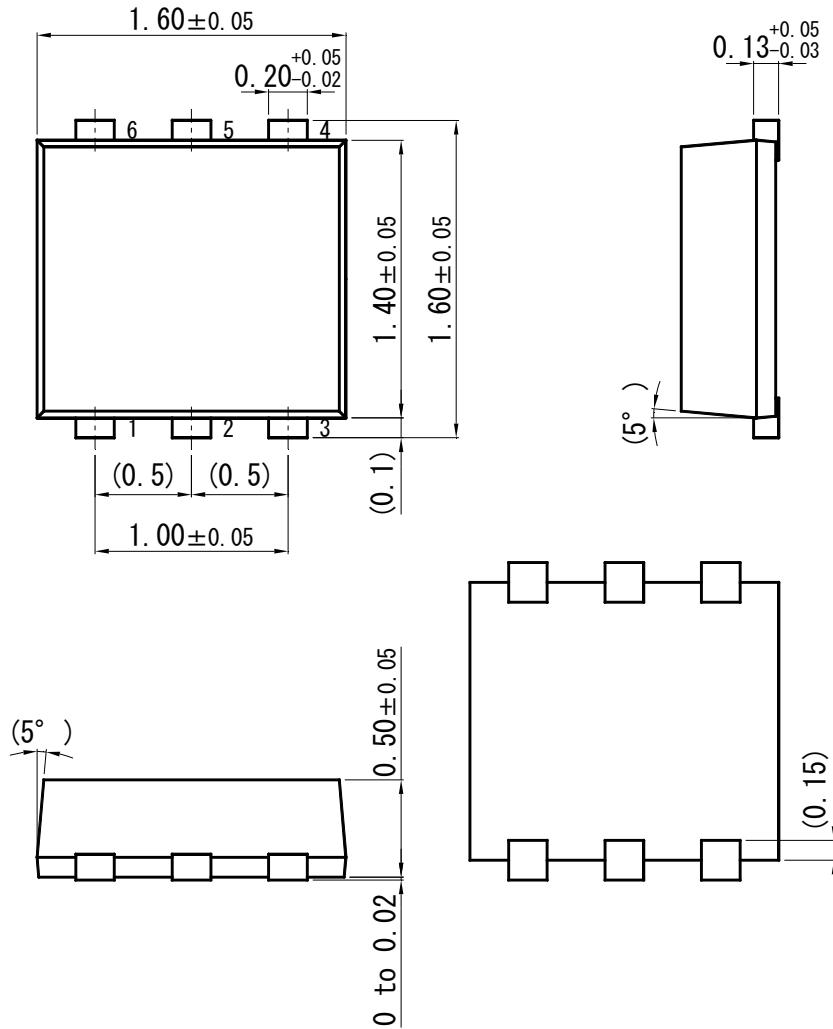


Technical Data (reference)

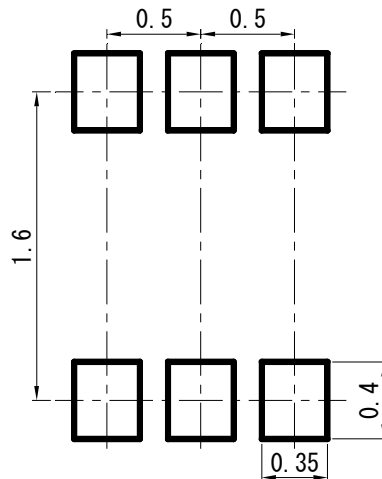


WSSMini6-F1

Unit: mm



■ Land Pattern (Reference) (Unit : mm)



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